

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		S24 near10 (thermal or heating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:15
		S4 and (dose same nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:34
L1	0	silicon oxynitride near nitiding near plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 10:55
L2	0	silicon oxynitride near nitriding near plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 10:55
L3	0	silicon oxynitride near nitriding andplasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 10:55

L4	7	silicon oxynitride near nitriding and plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 10:55
L5	68	silicon oxynitride same nitriding near plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 10:55
L6	13	I5 and wet etching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 11:21
L7	0	I5 and wet etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 11:24
L8	20	I5 and wet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 11:24
L9	87	silicon oxide and (trench near wet etch\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 11:25

S1	749	(rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 09:42
S2	577	S1 and pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 09:42
S3	10	S2 and lower pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 09:42
S4	74	S2 and reduced pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 09:42
S8	18	S4 and dose	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:32
S10	2	S4 and (dose same nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:34

S11	23	S4 and (dose or concentration same nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:34
S13	3	S4 and ppm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:37
S14	211	(rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification) and (dose or ppm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:38
S15	14	(rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and ((nitrogen or nitride or nitrification) near5 (dose or ppm))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 10:39
S16	0	438/197,261,287,591,770,773,775,787,788,792	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 16:26
S17	8589	438/197,261,287,591,770,773,775,787,788,792.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 16:26

S18	749	(rapid thermal oxidation or RTO or rapid thermal oxidizing) and etch\$3 and plasma and (nitrogen or nitride or nitrification)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 16:26
S19	109	S17 and S18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 16:26
S20	13	S19 and reduced pressure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/07 16:26
S21	101	"5,939,763"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:07
S22	2	"5,939,763".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:07
S23	9388	thin\$4 near (silicon oxide or "SiO.sub.2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:10

S24	7477	S23 and (thermal or heat\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:10
S25	564	S24 and thinning	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:11
S26	95	thinning near (silicon oxide or "SiO.sub.2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:11
S27	77	S26 and (thermal or heating\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:11
S28	1	S26 near (thermal or heating\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:14
S29	0	("2008/0096395").URPN.	USPAT	ADJ	ON	2009/04/13 09:15
S30	0	("2008/0096395").URPN.	USPAT	ADJ	ON	2009/04/13 09:15

S31	692	S23 near10 (thermal or heating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:15
S32	356	"I19" and annealing	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:16
S33	322	"I16" and annealing	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:16
S34	271	S31 and annealing	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/13 09:16

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